LINEAR SYSTEMS

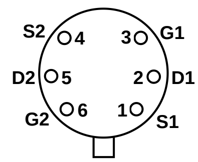
Over 30 Years of Quality Through Innovation

LSK389 A/B/C/D

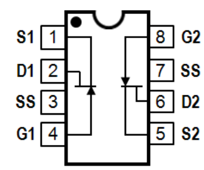
Ultra Low Noise Monolithic Dual N-Channel JFET Amplifier

INDUSTRY'S FIRST 100% TESTED LOWEST NOISE JFET

Absolute Maximum Ratings @ 25 °C (unless otherwise stated)	
Maximum Temperatures	
Storage Temperature	-65 to +150°C
Junction Operating Temperature	-55 to +150°C
Maximum Power Dissipation	
Continuous Power Dissipation @ +25°C	400mW
Maximum Currents	
Gate Forward Current	$I_{G(F)}$ = 10mA
Maximum Voltages	
Gate to Source	V_{GSS} = 40V
Gate to Drain	V_{GDS} = 40V



TO-71 6L Top View



SOIC 8L Top View

Features

- Ultra Low Noise: e_n = 1.3nV/√Hz (typ), f = 1.0kHz and NBW = 1.0Hz
- Ultra Low Noise: 1.5nV/√Hz (typ), f = 10Hz and NBW = 1.0Hz
- Tight Matching: $|V_{GS1-2}|$ = 15mV max
- High Breakdown Voltage: BV_{GSS} = 40V max
- High Gain: G_{fs} = 20mS (typ)
- Low Capacitance: 25pF (typ)
- Improved Second Source Replacement for 2SK389

Benefits

- Improved System Noise Performance
- Unique Monolithic Dual Design Construction of Interleaving Both JFETs on the Same Piece of Silicon
- Excellent Matching and Thermal Tracking
- Great for Maximizing Battery Operated Applications by Providing a Wide Output Swing
- A High Signal to Noise Ratio as a Result of the LSK389's Low and Tightly Matched Gate Threshold Voltages

Applications

- Audio Amplifiers and Preamps
- Discrete Low-Noise Operational Amplifiers
- Battery-Operated Audio Preamps
- Audio Mixer Consoles
- Acoustic Sensors
- Sonic Imaging
- Instrumentation Amplifiers
- Microphones
- Sonobouys
- Hydrophones
- Chemical and Radiation Detectors

Description

The LSK389 is the industry's lowest noise Dual N-Channel JFET, 100% tested, guaranteed to meet 1/*f* and broadband noise specifications, while eliminating burst (RTN or popcorn) noise entirely. The LSK389 Series, Monolithic Dual N-Channel JFETs were specifically designed to provide users a better performing, less time consuming and cheaper solution for obtaining tighter IDSS matching, and better thermal tracking, than matching individual JFETs. The LSK389's features incorporate four grades of IDSS: 2.6-6.5mA, 6.0-12.0mA, 10.0-20.0mA and 17-30mA, with an IDSS match of 10 percent, a gate threshold offset of 15mV, a voltage noise (en) of 1.3nV/√Hz typical at f = 1.0kHZ, with a Gain of 20mS typical, and 25pF of capacitance typical. The LSK389 provides a wide output swing, and a high signal to noise ratio as a result of the LSK389's tightly matched and low gate threshold voltages. The 40V breakdown provides maximum linear headroom in high transient program content amplifiers.
Additionally, the LSK389 provides a low input noise to capacitance product that has nearly zero popcorn noise. The narrow ranges of the IDSS electrical grades combined with the superior matching performance of the LSK389's monolithic dual construction promote ease of device tolerance in low voltage applications, as compared to matching single JFETs. Available in surface mount SOIC 8L and thru-hole TO-71 6L packages.
Contact the factory for tighter noise and other specification selections. For equivalent single N-Channel version, please refer to the LSK170 datasheet.

Ultra Low Noise Monolithic Dual N-Channel JFET Amplifier

Electrical Characteristics @ 25°C (unless otherwise stated)

SYMBOL	CHARACTERISTIC		MIN	TYP	MAX	UNITS	CONDITIONS
BV_{GSS}	Gate to Source Breakdown Voltage		-40	---	---	V	V_{DS} = 0, I_D = -100µA
$V_{GS(OFF)}$	Gate to Source Pinch-off Voltage		-0.3	---	-1.6	V	V_{DS} = 10V, I_D = 0.1µA
I_{DSS}	Drain to Source Saturation Current	LSK389A	2.6	---	6.5	mA	V_{DS} = 10V, V_{GS} = 0
		LSK389B	6	---	12		
		LSK389C	10	---	20		
		LSK389D	17	---	30		
I_{GSS}	Gate to Source Leakage Current		---	-100	-300	pA	V_{GS} = -25V, V_{DS} = 0
I_{G1G2}	Gate to Gate Isolation Current		---	±1.0	±50	nA	V_{G1-G2} = ±45V, I_D = I_S = 0A
G_{fs}	Full Conduction Transconductance		8	20	---	mS	V_{DS} = 10V, V_{GS} = 0, *f* = 1kHz
e_n	Noise Voltage		---	1.3	1.9	nV/√Hz	V_{DS} = 10V, I_D = 2mA, *f* = 1kHz, NBW = 1Hz
e_n	Noise Voltage		---	1.5	4.0	nV/√Hz	V_{DS} = 10V, I_D = 2mA, *f* = 10Hz, NBW = 1Hz
C_{ISS}	Common Source Input Capacitance		---	25	---	pF	V_{DS} = 10V, V_{GS} = 0, *f* = 1MHz,
C_{RSS}	Common Source Reverse Transfer Cap.		---	5.5	---	pF	V_{DG} = 10V, I_D = 0, *f* = 1MHz,

Matching Characteristics @ 25°C (unless otherwise stated)

SYMBOL	CHARACTERISTIC	MIN	TYP	MAX	UNITS	CONDITIONS
$\lvert V_{GS1} - V_{GS2} \rvert$	Differential Gate to Source Cutoff Voltage	---	6.0	15	mV	V_{DS} = 10V, I_D = 1mA
$\frac{I_{DSS1}}{I_{DSS2}}$	Saturation Drain Current Ratio	0.9	1.0	1.1	n/a	V_{DS} = 10V, V_{GS} = 0V

Notes

1. Absolute maximum ratings are limiting values above which serviceability may be impaired.
2. Pulse Test: PW ≤ 300µs, Duty Cycle ≤ 3%
3. All characteristics MIN/TYP/MAX numbers are absolute values. Negative values indicate electrical polarity only.

Typical Characteristics

LSK389A

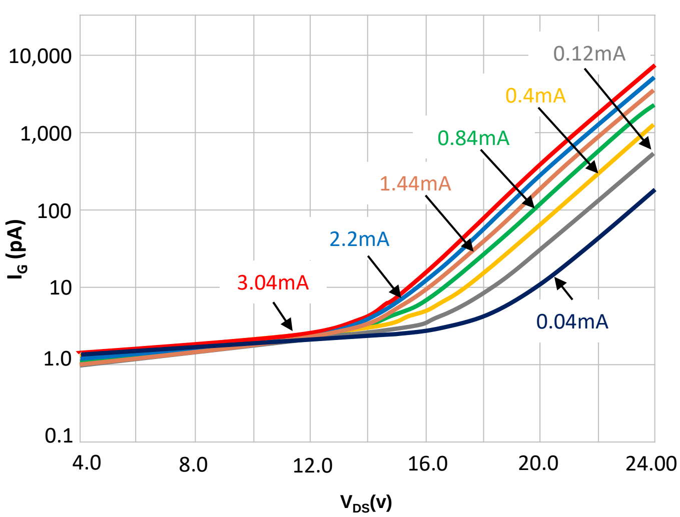


Figure 1. Gate Current (I_G) vs. V_{DS} vs. I_D

LSK389B

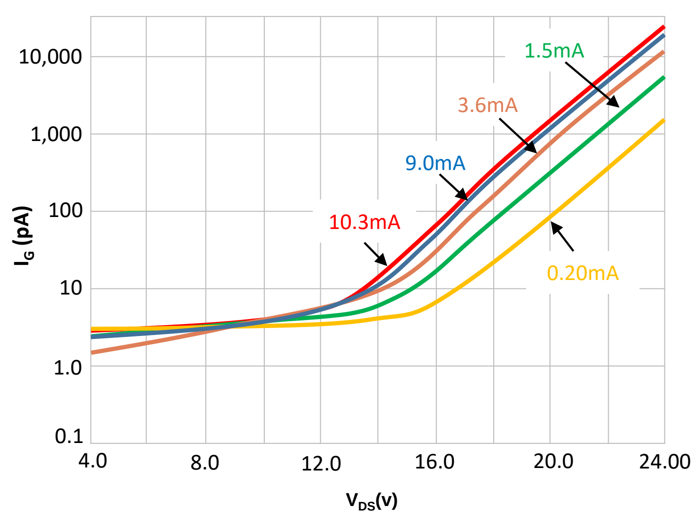


Figure 2. Gate Current (I_G) vs. V_{DS} vs. I_D

LSK389C

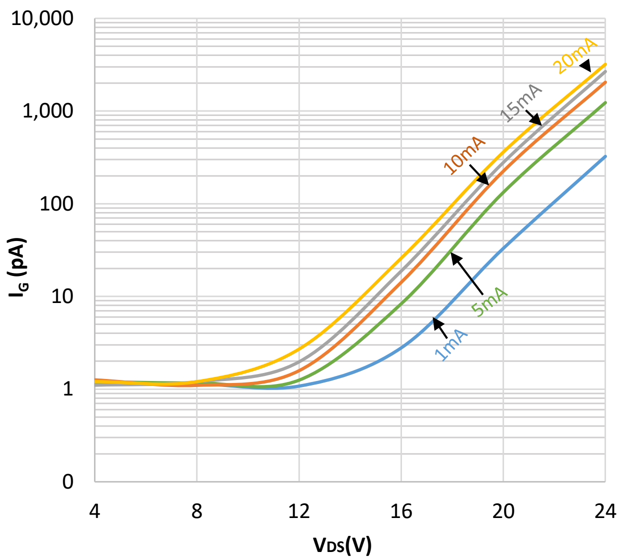


Figure 3. Gate Current (I_G) vs. V_{DS} vs. I_D

LSK389D

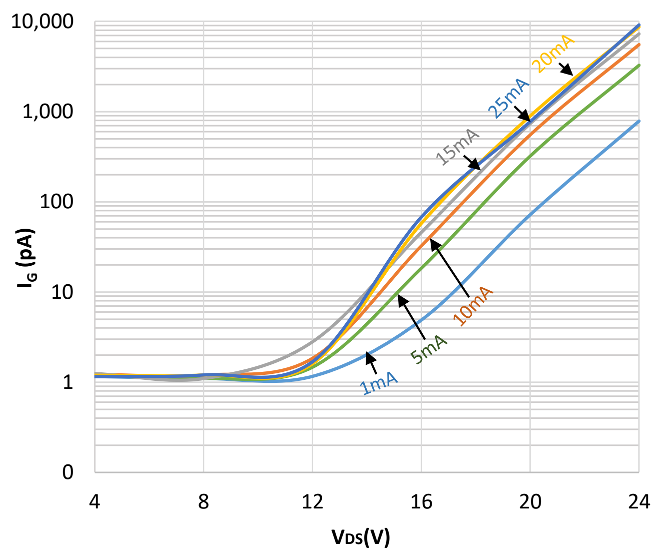


Figure 4. Gate Current (I_G) vs. V_{DS} vs. I_D

Typical Characteristics

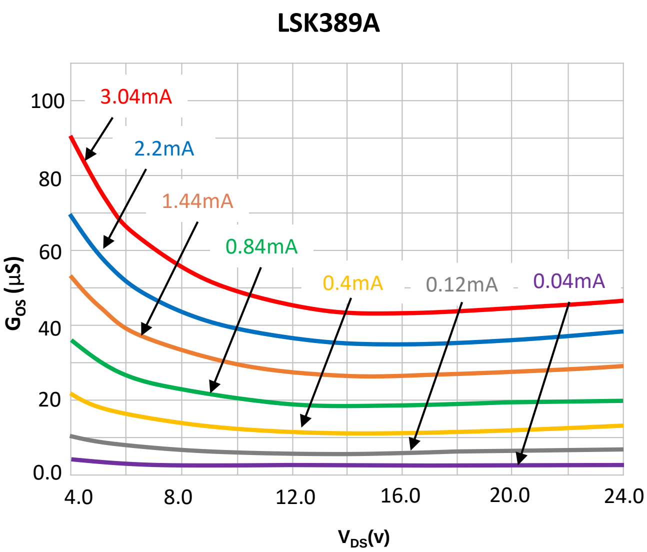


Figure 5. Output Conductance - G_{OS} vs. V_{DS} vs. I_D

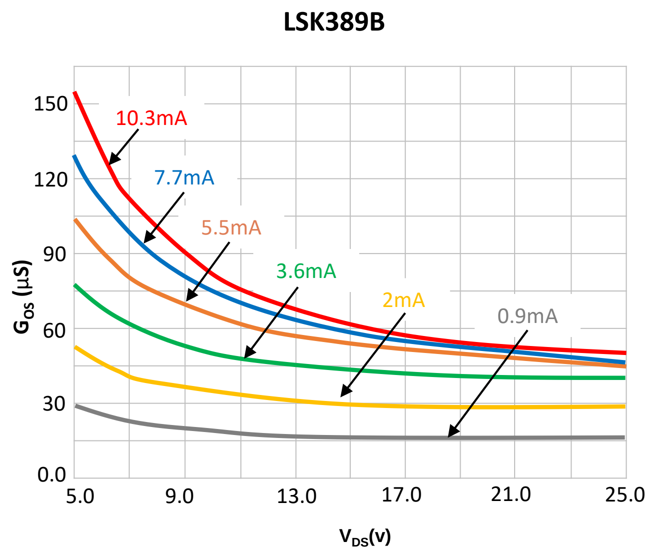


Figure 6. Output Conductance - G_{OS} vs. V_{DS} vs. I_D

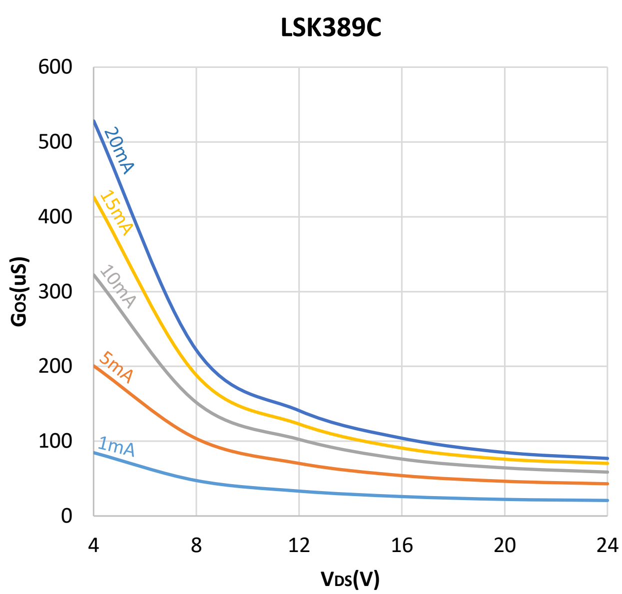


Figure 7. Output Conductance - G_{OS} vs. V_{DS} vs. I_D

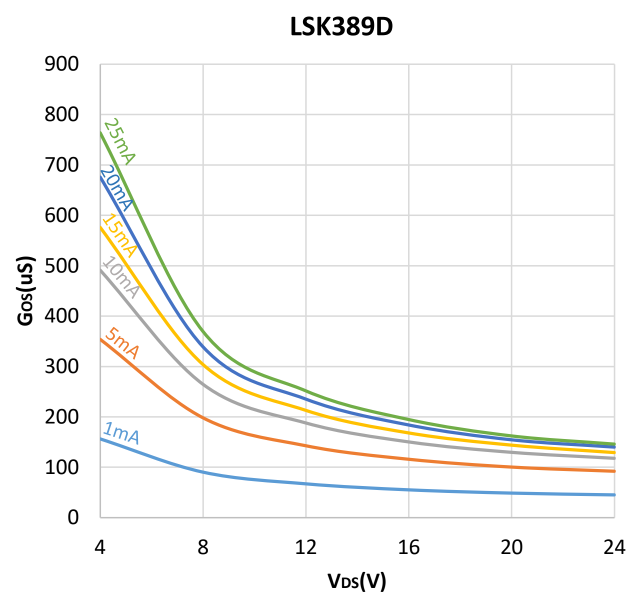


Figure 8. Output Conductance - G_{OS} vs. V_{DS} vs. I_D

Typical Characteristics

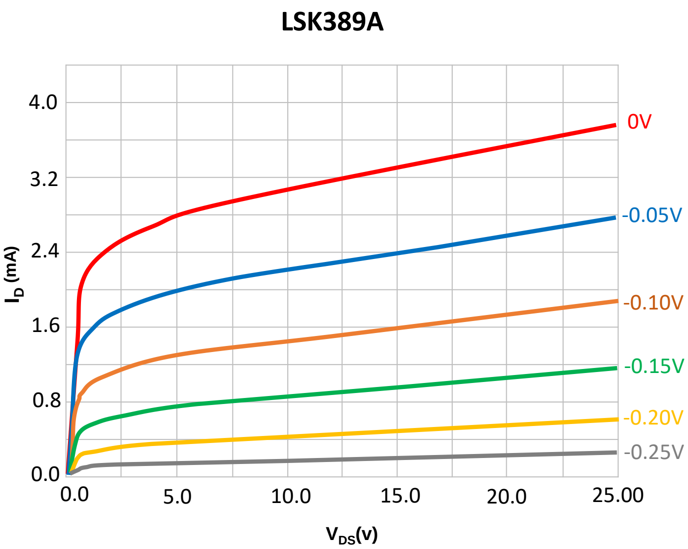


Figure 9. I_D vs. V_{DS} vs. V_{GS}

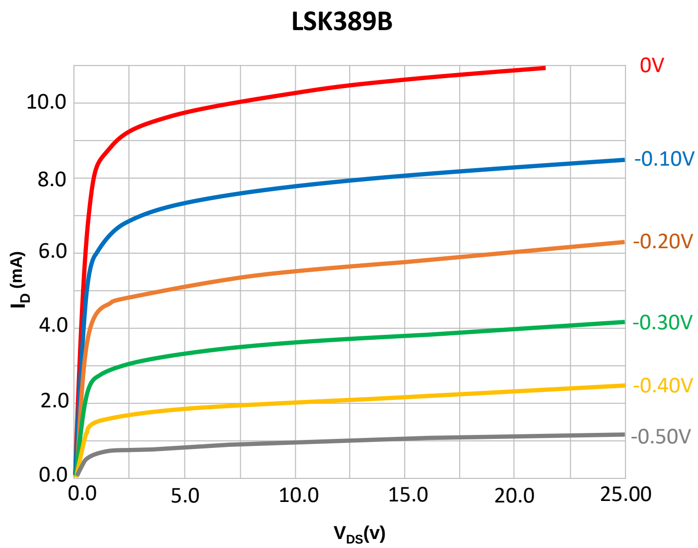


Figure 10. I_D vs. V_{DS} vs. V_{GS}

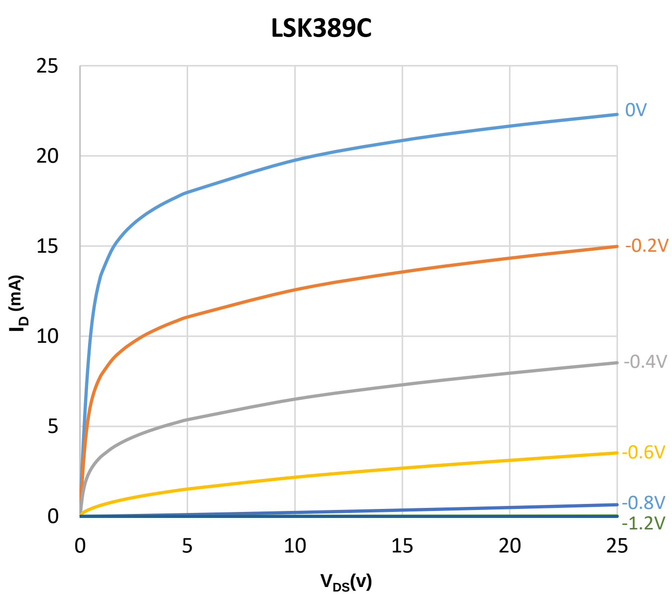


Figure 11. I_D vs. V_{DS} vs. V_{GS}

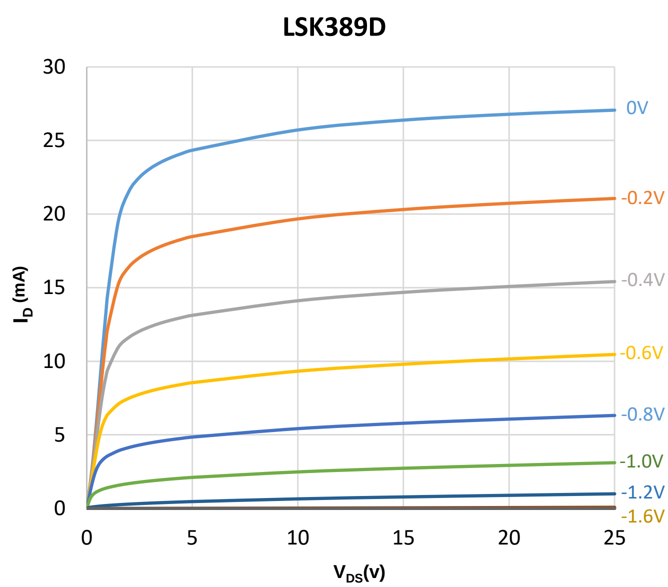


Figure 12. I_D vs. V_{DS} vs. V_{GS}

Typical Characteristics

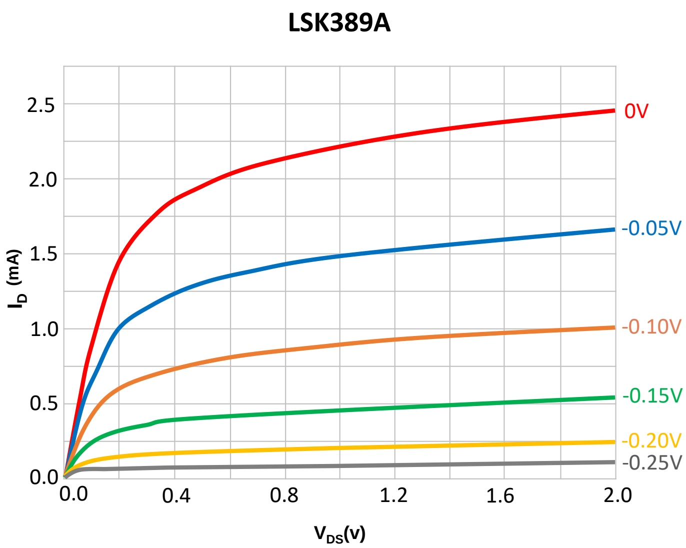


Figure 13. I_D vs. V_{DS} vs. V_{GS}

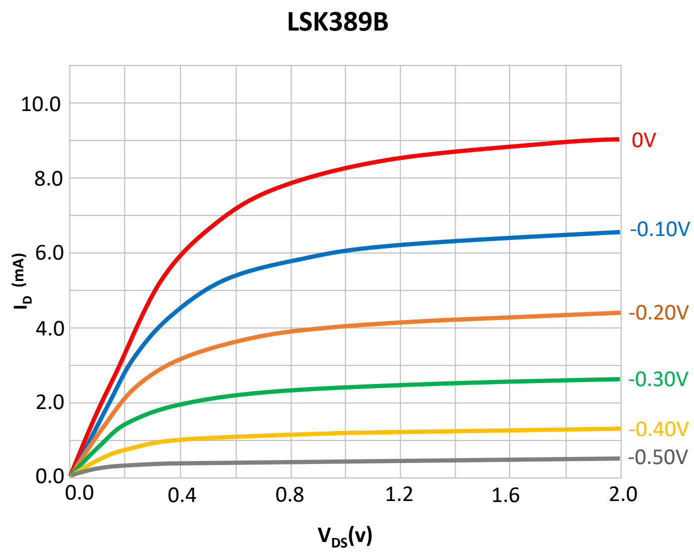


Figure 14. I_D vs. V_{DS} vs. V_{GS}

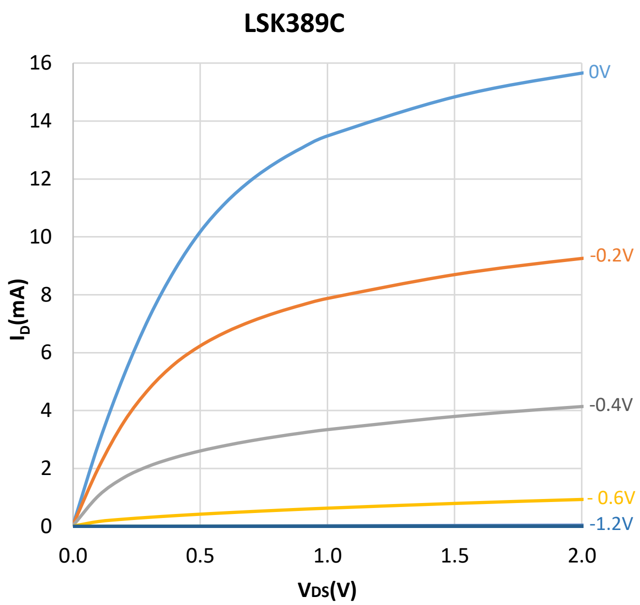


Figure 15. I_D vs. V_{DS} vs. V_{GS}

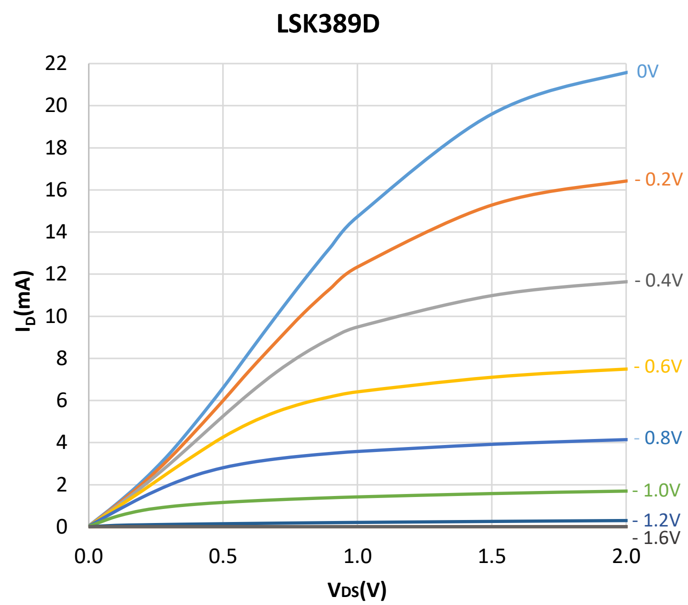


Figure 16. I_D vs. V_{DS} vs. V_{GS}

Typical Characteristics

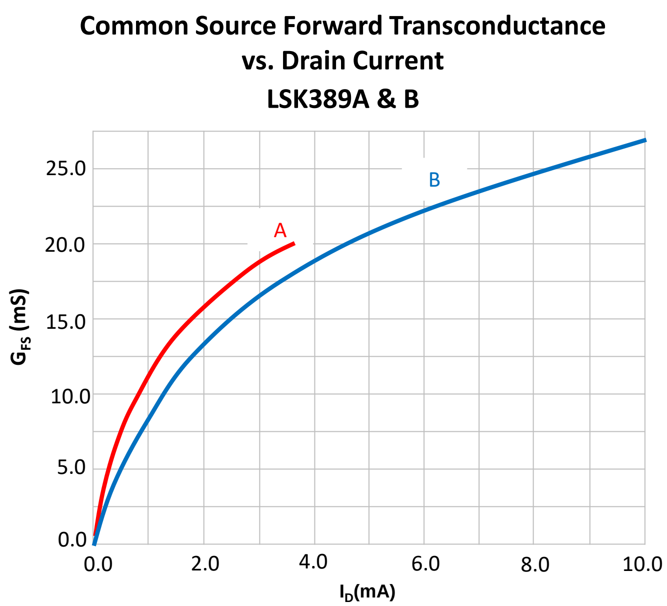


Figure 17. G_{FS} vs. I_D

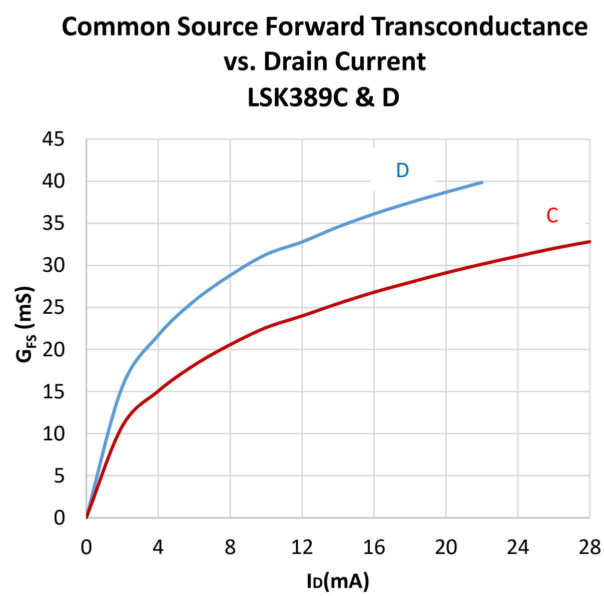


Figure 18. G_{FS} vs. I_D

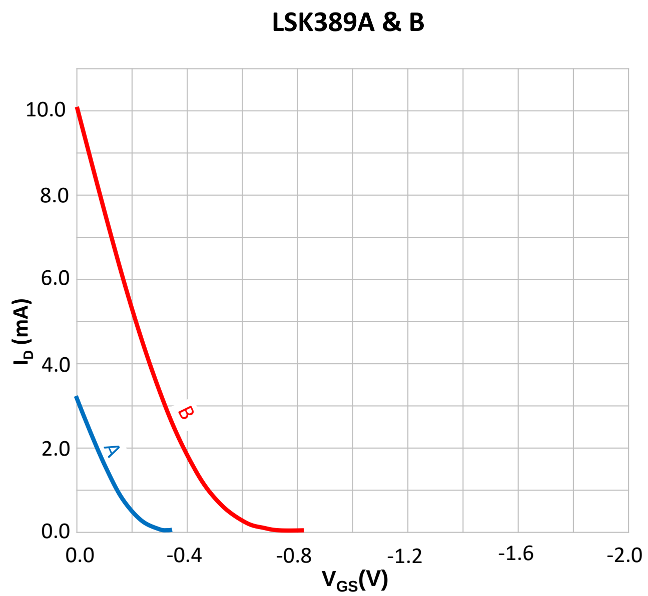


Figure 19. I_D vs. V_{GS}

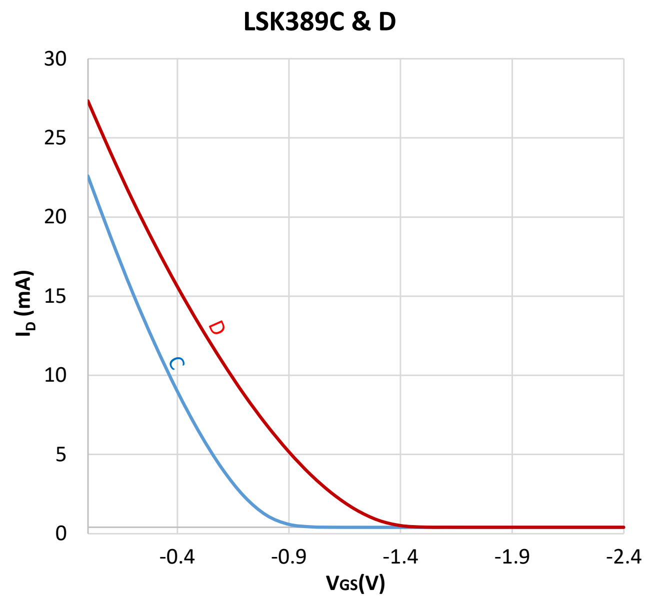


Figure 20. I_D vs. V_{GS}

Typical Characteristics

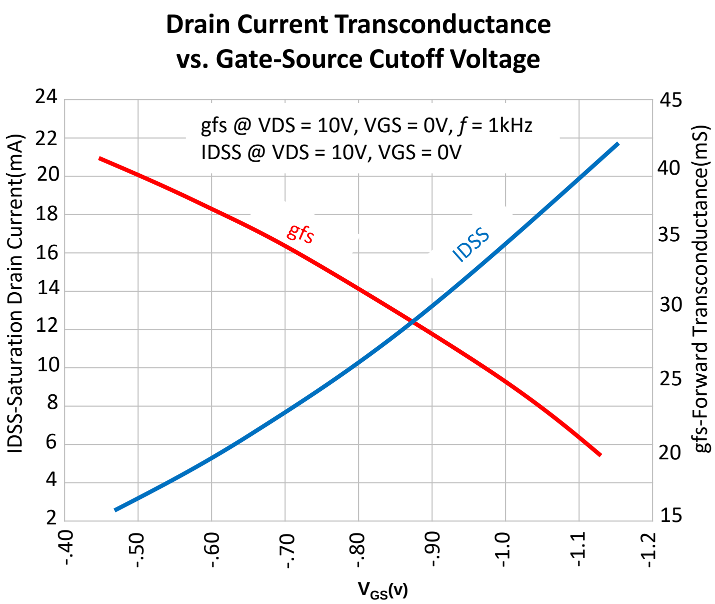


Figure 21. V_{GS} (cutoff) vs. I_{DSS} vs. G_{FS}

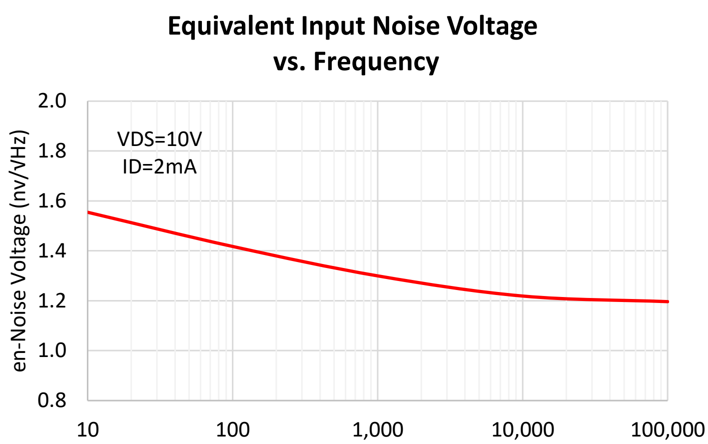
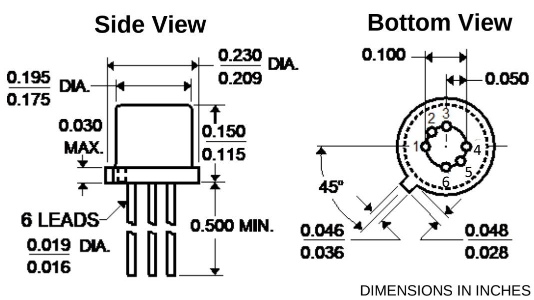


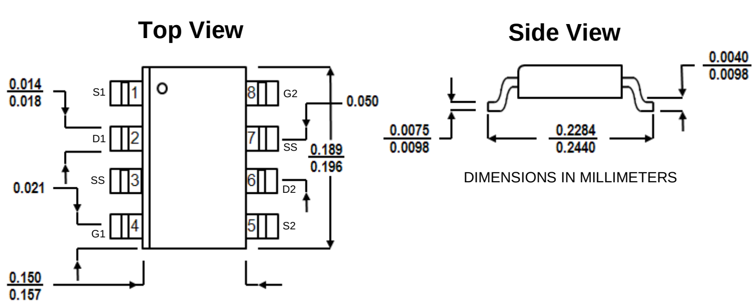
Figure 22.
f - Frequency (Hz)

Package Dimensions

TO-71 6 Lead



SOIC 8 Lead



SS: SUBSTRATE, LEAVE THESE PINS FLOATING (N/C)

Ordering Information

Standard Part Call-Out
LSK389A/B/C or D TO-71 6L RoHS
LSK389A/B/C or D SOIC 8L RoHS
Custom Part Call-Out (Custom Parts Include SEL + 4 Digit Numeric Code)
LSK389A/B/C or D TO-71 6L RoHS SELXXXX
LSK389A/B/C or D SOIC 8L RoHS SELXXXX